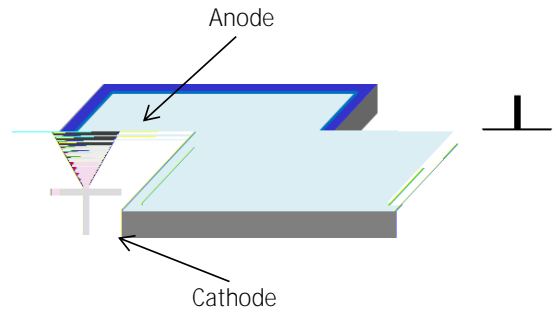


# YJ Planar Schottky Barrier Diode Die Specification

40V 5A, 65mil, Schottky barrier diode die based on silicon planar process  
 Part No.: PSB065M040SS-280A



## Main Products Characteristics

### Maximum Ratings

Parameter	Symbol	Rating
Repetitive peak reverse voltage	$V_{RRM}$	40 V
Average forward current	$I_{F(AV)}$	5 A
( $t_p = 8.3$ ms, halfwave, 1 cycle)	$I_{FSM}$	120 A
Storage temperature range	$T_{stg}$	-50 to +150 °C
Maximum operating junction temperature	$T_j$	150 °C

### Static Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	
		Spec	Typical
Reverse breakdown voltage $I_R = 1\text{mA}$	$V_{BR}$	45 V	52V
Maximum forward voltage drop $I_F = 5\text{A}$ 2%	$V_F$	0.53V	0.50V
Maximum reverse current $V_R = V_{RRM}$ 2%	$I_R$	50uA	20uA

## Device Schematics and Outline Drawing

Die Thickness *	11 Mils
Die Size **	65 Mils
Top Metal Pad	60.6 Mils
Active Area	57 Mils
Top Metal	Ag
Back Metal	Ag

Note: 1 \* : Also can offer device with 8 mils thickness  
 2 \*\*: Cutting street width is around 1.5 mils

## Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

does not guarantee device performance after assembly.  
 All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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